



## 1. Description

N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS™ technology.

Product availability:

PMN28UN in SOT457 (TSOP6).

## 2. Features

- TrenchMOS™ technology
- Very fast switching
- Low threshold voltage
- Surface mount package.

## 3. Applications

- Battery powered motor control
- Load switch in notebook computers
- High speed switch in set top box power supplies
- Driver FET in DC to DC converters.

## 4. Pinning information

Table 1: Pinning - SOT457 (TSOP6), simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1,2,5,6	drain (d)	<p>Top view <span style="float: right;">MBK092</span></p> <p><b>SOT457 (TSOP6)</b></p>	<p>MBB076</p>
3	gate (g)		
4	source (s)		

## 5. Quick reference data

**Table 2: Quick reference data**

Symbol	Parameter	Conditions	Typ	Max	Unit
$V_{DS}$	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	12	V
$I_D$	drain current (DC)	$T_{sp} = 25\text{ °C}; V_{GS} = 4.5\text{ V}$	-	5.7	A
$P_{tot}$	total power dissipation	$T_{sp} = 25\text{ °C}$	-	1.75	W
$T_j$	junction temperature		-	150	°C
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 2\text{ A}; T_j = 25\text{ °C}$	28	34	mΩ
		$V_{GS} = 2.5\text{ V}; I_D = 2\text{ A}; T_j = 25\text{ °C}$	32	40	mΩ
		$V_{GS} = 1.8\text{ V}; I_D = 1.5\text{ A}; T_j = 25\text{ °C}$	39	56	mΩ

## 6. Limiting values

**Table 3: Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	12	V
$V_{GS}$	gate-source voltage (DC)		-	±8	V
$I_D$	drain current (DC)	$T_{sp} = 25\text{ °C}; V_{GS} = 4.5\text{ V};$ <b>Figure 2 and 3</b>	-	5.7	A
		$T_{sp} = 70\text{ °C}; V_{GS} = 4.5\text{ V};$ <b>Figure 2</b>	-	4.5	A
$I_{DM}$	peak drain current	$T_{sp} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s};$ <b>Figure 3</b>	-	22.9	A
$P_{tot}$	total power dissipation	$T_{sp} = 25\text{ °C};$ <b>Figure 1</b>	-	1.75	W
$T_{stg}$	storage temperature		-55	+150	°C
$T_j$	junction temperature		-55	+150	°C

### Source-drain diode

$I_S$	source (diode forward) current (DC)	$T_{sp} = 25\text{ °C}$	-	1.45	A
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